



#### N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI<sup>®</sup>

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>C</sub> = +25℃
30V	8.5mΩ @ V <sub>GS</sub> = 10V	30A
300	$10.5m\Omega @ V_{GS} = 4.5V$	25A

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

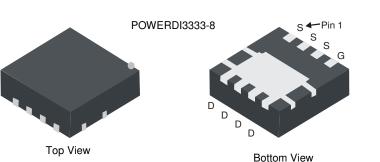
- Backlighting
- DC-DC Converters
- Power Management Functions

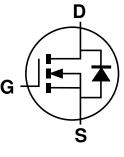
#### Features

- Low R<sub>DS(ON)</sub> ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- 100% Rg tested
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)





Equivalent Circuit

#### Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN3010LFG-7	Standard	POWERDI3333-8	2,000/Tape & Reel
DMN3010LFG-13	Standard	POWERDI3333-8	3,000/Tape & Reel

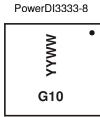
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



 $\begin{array}{l} G10 = Product \ Marking \ Code \\ YYWW = Date \ Code \ Marking \\ YY = Last \ Digit \ of \ Year \ (ex: \ 15 \ for \ 2015) \\ WW = Week \ Code \ (01 - 53) \end{array}$ 

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### Maximum Ratings (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteris	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
	Steady State	T <sub>A</sub> = +25 ℃ T <sub>A</sub> = +70 ℃	ID	11 8.5	A
Continuous Drain Current (Note 6) $V_{GS} = 10V$	t<10s	T <sub>A</sub> = +25 ℃ T <sub>A</sub> = +70 ℃	Ι <sub>D</sub>	14 11	А
Continuous Drain Current (Note 6) $V_{GS}$ = 10V	Steady State	T <sub>C</sub> = +25℃ T <sub>C</sub> = +100℃	ID	30 20	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%	I <sub>DM</sub>	90	A		
Avalanche Current (Note 7) L = 0.1mH	IAS	12.7	A		
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	8.1	mJ		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	137	°C/W
Thermal Resistance, Junction to Amblent (Note 5)	t < 10s	R <sub>0JA</sub>	90	°C/W
Total Power Dissipation (Note 6)		PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	52	°C/W
Thermal Resistance, Junction to Amblent (Note 6)	t < 10s	R <sub>θJA</sub>	35	°C/W
Total Power Dissipation (Note 6)	Tc = +25 ℃	PD	26	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	4.8	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	—	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25 °C		_	—	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +150 ℃ (Note 9)	IDSS	_	-	100	μA	$v_{\rm DS} = 30v, v_{\rm GS} = 0v$	
Gate-Source Leakage	I <sub>GSS</sub>	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)			-				
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	6.5	8.5	mΩ	$V_{GS} = 10V, I_D = 18A$	
Static Drain-Source On-nesistance	R <sub>DS(ON)</sub>	—	8	10.5	11152	$V_{GS} = 4.5V, I_D = 16A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
On State Drain Current (Note 9)	I <sub>D(ON)</sub>	10	—	—	А	$V_{DS} \leq 5V, V_{GS} = 4.5V$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	—	2,075	4,150		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	190	380	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	138	276			
Gate Resistance	Rq	_	2.4	5	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qq	_	16.1	32			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qq	_	37	74			
Gate-Source Charge	Q <sub>qs</sub>	_	6.1	12	nC	$V_{DS} = 15V, I_D = 18A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	5.9	12			
Turn-On Delay Time	t <sub>D(on)</sub>	_	4.5	10			
Turn-On Rise Time	tr	_	19.6	35		$V_{DS} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	31	50	ns	$R_L = 0.83\Omega$ , $R_{GEN} = 3\Omega$ ,	
Turn-Off Fall Time	tf	_	10.7	21			
Reverse Recovery Time	t <sub>rr</sub>	_	13.7	27	ns		
Reverse Recovery Charge	Qrr	_	18.3	37	nC	I <sub>F</sub> =15A, di/dt=500A/μs	
Notes: 5. Device mounted on FR-4 substrate PC board, 202	copper, with r	ninimum rea	commended p	bad layout.			

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.

7. UIS in production with L = 1mH, TJ =  $+25 \degree$ C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.

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# DMN3010LFG

T<sub>A</sub> = 25 ℃

-55℃

4

5

T<sub>A</sub> = 150 ℃

T<sub>A</sub> = 85℃

T<sub>A</sub> = -55℃

T<sub>A</sub> = 25℃

25

30

3

-T<sub>A</sub> = 125 ℃

15

10

25

50

75

20

 $V_{GS} = 5.0V$ 

 $V_{GS} = 10V$ 

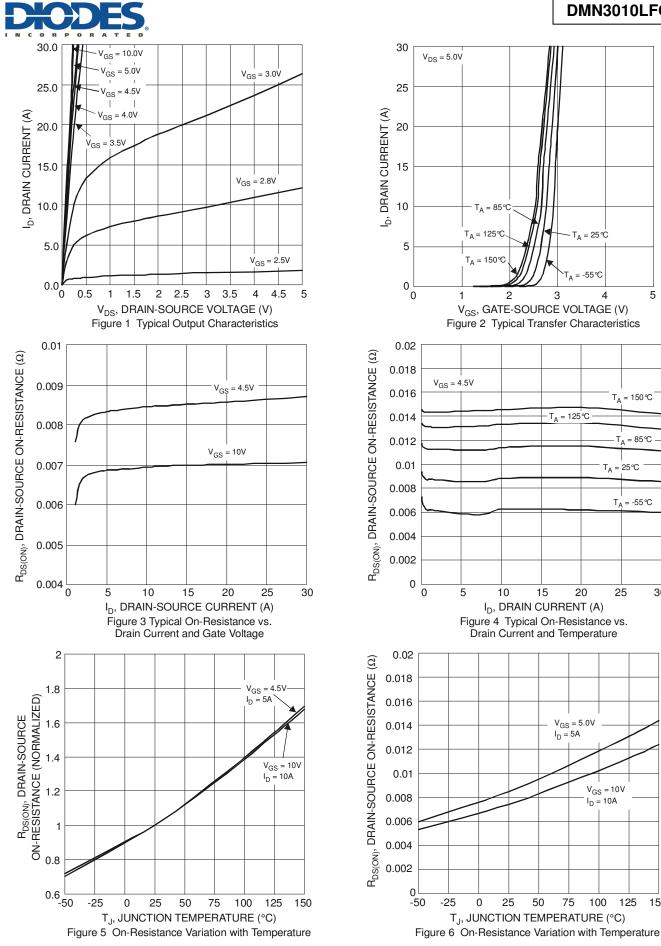
I<sub>D</sub> = 10A

100

125

I<sub>D</sub> = 5A

2

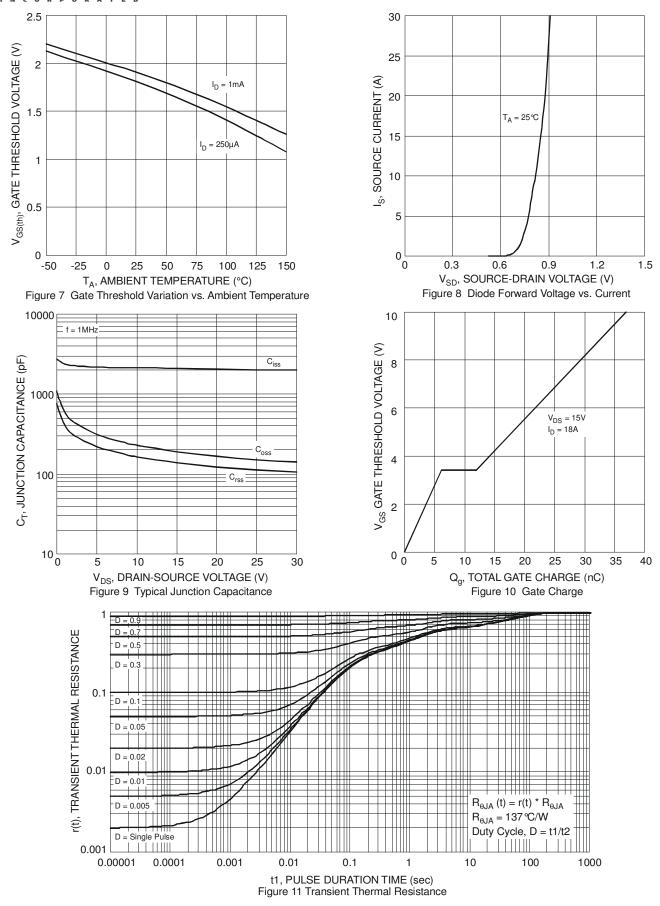


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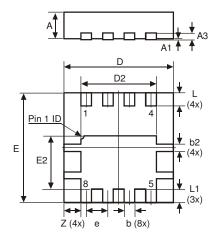
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## **Package Outline Dimensions**

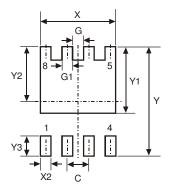
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI <sup>®</sup> 3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
E	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	-	-	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All	All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.420			
Y	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
Х	2.370			
X2	0.420			



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